

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2	"20030178674"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/30 12:50
S2	1985	@ad<="20020322" and (257/410-413).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 12:57
S3	143	@ad<="20020322" and (438/216).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 12:57
S4	318	@ad<="20020322" and (438/261).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/30 10:57
S5	713	@ad<="20020322" and (438/287).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/30 10:58
S6	844	@ad<="20020322" and (438/585).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/30 11:00
S7	448	@ad<="20020322" and (438/587-588).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/30 11:00
S8	317	@ad<="20020322" and (438/591).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/30 11:04
S9	298	@ad<="20020322" and (438/791).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/30 11:04
S10	196	@ad<="20020322" and (438/792).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/30 11:05

## EAST Search History

S11	50	@ad<="20020322" and 'MOS' same 'high dielectric' with 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/30 11:10
S12	9	@ad<="20020322" and 'MOS' same 'Hafnium oxide' with 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/29 14:38
S13	196	@ad<="20020322" and 'MOS' same 'aluminum oxide' with 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/30 12:06
S14	16	@ad<="20020322" and 'high dielectric' same 'aluminum oxide' same 'nitride layer'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/30 11:33
S15	3	@ad<="20020322" and 'MOS' same 'high dielectric constant' same 'nitridation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/14 16:02
S16	302	@ad<="20020322" and 'high dielectric constant' and 'nitridation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/31 07:55
S17	14	@ad<="20020322" and 'high dielectric constant' and 'plasma nitriding'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/30 12:09
S18	2	"20020137317"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/30 12:23
S19	2	("6482694").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/12/30 12:24
S20	2	("6339246").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/12/30 12:24

## EAST Search History

S21	24	bai-gang.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/30 12:51
S22	50	@ad<="20020322" and 'nitridation' same 'high dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/29 14:05
S23	5	@ad<="20020322" and 'plasmas' adj1 'nitridation' same 'high dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/31 07:56
S24	3	@ad<="20020322" and 'plasmas' adj1 'nitriding' same 'high dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/31 07:56
S25	5	@ad<="20020322" and 'plasma nitridation' same 'high dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/31 08:15
S26	162	@ad<="20020322" and 'nitride layer' with 'high dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/31 08:33
S27	128	@ad<="20020322" and 'nitride layer' with 'tantalum oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/31 08:49
S28	76	@ad<="20020322" and 'polysilicon' same 'tantalum oxide' same 'nitride layer'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/31 08:32
S29	46	@ad<="20020322" and 'nitride layer' with 'high k'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/17 11:24
S30	102	@ad<="20020322" and 'p-type polysilicon gate' same 'n-type polysilicon gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/31 10:33
S31	140	@ad<="20020322" and 'p-type polysilicon' with 'boron'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/31 10:35

## EAST Search History

S32	35	@ad<="20020322" and 'p-type polysilicon gate' with 'boron'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/12/31 10:36
S33	1	"6291868".PN.	USPAT	OR	OFF	2003/12/31 10:42
S34	2	("6436848").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/04/29 13:29
S35	36	@ad<="20020322" and 'nitridation' same 'high k'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/29 14:05
S36	415	@ad<="20020322" and "'HfO.sub.2'" same 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/29 14:40
S37	175	@ad<="20020322" and "'HfO.sub.2'" same "'ZrO.sub.2'" with 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/07 15:26
S38	19	@ad<="20020322" and 'high k' same "'HfO.sub.2'" same "'ZrO.sub.2'" with 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/29 14:40
S39	43	@ad<="20020322" and 'high k' and "'HfO.sub.2'" same "'ZrO.sub.2'" with 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/29 14:41
S40	54	@ad<="20020322" and 'high dielectric' and "'HfO.sub.2'" same "'ZrO.sub.2'" with 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/29 15:09
S41	2	"20010053601"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/29 15:04
S42	3	@ad<="20020322" and 'MIS' and 'high dielectric' and "'HfO.sub.2'" same 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/29 15:10

## EAST Search History

S43	2	"20020089023"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/29 15:27
S44	10	@ad<="20020322" and ""Al.sub.2O.sub.3"" same 'nitridation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/07 15:02
S45	5	@ad<="20020322" and ""HfO.sub.2"" same 'nitridation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/07 14:57
S46	12	@ad<="20020322" and ""ZrO.sub.2"" same 'nitridation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/07 14:58
S47	13	@ad<="20020322" and ""Al.sub.2O.sub.3"" with 'nitride' adj1 'layer'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/07 15:03
S48	180	@ad<="20020322" and ""HfO.sub.2"" with ""ZrO.sub.2"" with 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/07 15:26
S49	42	@ad<="20020322" and 'MOS' and ""HfO.sub.2"" with ""ZrO.sub.2"" with 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/07 15:39
S50	128	@ad<="20020322" and 'MOS' and 'high k' with 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/07 15:39
S51	741	@ad<="20020322" and (257/310). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 10:28
S52	551	@ad<="20020322" and (257/410). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 10:29
S53	531	@ad<="20020322" and (257/411). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/14 15:33

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S54	957	@ad<="20020322" and (257/412). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/14 15:33
S55	411	@ad<="20020322" and (257/413). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/14 15:33
S56	153	@ad<="20020322" and (438/216). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/14 15:51
S57	855	@ad<="20020322" and (438/240). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/14 15:51
S58	24	@ad<="20020322" and 'MOS' same 'high dielectric' with 'gate' same 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/14 16:12
S59	21	@ad<="20020322" and 'MOS' same 'gate' with 'high k' same 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/14 16:13
S60	2067	@ad<="20020322" and (257/410-413).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 10:02
S61	1	"6297539".PN.	USPAT; USOCR	OR	ON	2005/09/30 10:20
S62	1	"6015739".PN.	USPAT; USOCR	OR	ON	2005/09/30 10:20
S63	1	"6013553".PN.	USPAT; USOCR	OR	ON	2005/09/30 10:21
S64	1	"4335391".PN.	USPAT; USOCR	OR	ON	2005/09/30 10:23
S65	1	"4151537".PN.	USPAT; USOCR	OR	ON	2005/09/30 10:23
S66	765	@ad<="20020322" and (257/310). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 12:58

## EAST Search History

S67	2080	@ad<="20020322" and (257/410-413).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 10:29
S68	161	@ad<="20020322" and (438/216).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 12:57
S69	770	@ad<="20020322" and (257/310).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 12:58
S70	6	@ad<="20020322" and "dielectric" with "PrO.sub.2"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 13:22
S71	6	@ad<="20020322" and "MOS" same "PrO.sub.2"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 13:07
S72	14	@ad<="20020322" and ("dielectric" or insulat\$3) same "PrO.sub.2"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 13:13
S73	14	((("4859904") or ("4963788") or ("4870322") or ("4758765") or ("4634639") or ("4455506") or ("4287449"))).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/22 13:14
S74	175	@ad<="20020322" and "dielectric" with ("PrO.sub.2" or "praseodymium")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 13:23
S75	230	@ad<="20020322" and "dielectric" same ("PrO.sub.2" or "praseodymium")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 13:23
S76	11	@ad<="20020322" and "gate dielectric" with ("PrO.sub.2" or "praseodymium")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 14:23

## EAST Search History

S77	3	@ad<="20020322" and "Pr.sub.2O.sub.3" with "PrO.sub.2"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 14:21
S78	3	@ad<="20020322" and "Pr.sub.2O.sub.3" same "PrO.sub.2"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 14:21
S79	7	@ad<="20020322" and "gate dielectric" with "praseodymium oxide"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 14:26
S80	7	@ad<="20020322" and "gate adj1(insulat\$3 or "dielectric") with "praseodymium oxide"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 14:27
S81	0	@ad<="20020322" and "gate insulator" with "praseodymium oxide"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 14:27
S82	0	@ad<="20020322" and "gate insulating" with "praseodymium oxide"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/22 14:27
S83	0	@ad<="20020322" and "Al.sub.2O.sub.3" same nitride and "LLD"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/17 11:25
S84	76	@ad<="20020322" and "high dielectric" with "Al.sub.2O.sub.3"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/17 11:42
S85	1684	@ad<="20020322" and ("high dielectric" or "high k") same "barrier"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/17 11:47
S86	313	@ad<="20020322" and ("FET" or "MOS" or "transistor") and ("high dielectric" or "high k") same "barrier" with nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/17 13:06
S87	451	@ad<="20020322" and ("high dielectric" or "high k") same "barrier" with nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/17 11:47



## EAST Search History

S88	17	@ad<="20020322" and ("FET" or "MOS" or "transistor") and ("high dielectric" or "high k") same "aluminum oxide" same "barrier" with nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/17 11:48
S89	17	@ad<="20020322" and ("FET" or "MOS" or "transistor") and ("high dielectric" or "high k") same "aluminum oxide" same "barrier" with nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/17 13:06
S90	18	@ad<="20020322" and ("FET" or "MOS" or "transistor") and ("high dielectric" or "high k") same ("aluminum oxide" or "Al.sub.2O.sub.3") same "barrier" with nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/17 13:21
S91	2	("6891231").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/17 13:21
S92	1	"6429052".PN.	USPAT; USOCR	OR	ON	2006/05/17 13:22
S93	1	"6407435".PN.	USPAT; USOCR	OR	ON	2006/05/17 13:24
S94	1	"6383873".PN.	USPAT; USOCR	OR	ON	2006/05/17 13:24
S95	1	"6340827".PN.	USPAT; USOCR	OR	ON	2006/05/17 13:30
S96	1	"6277681".PN.	USPAT; USOCR	OR	ON	2006/05/17 13:30
S97	1	"6107667".PN.	USPAT; USOCR	OR	ON	2006/05/17 13:30
S98	1	"6277681".PN.	USPAT; USOCR	OR	ON	2006/05/17 13:31
S99	1	"6020243".PN.	USPAT; USOCR	OR	ON	2006/05/17 13:31
S100	1	"6020024".PN.	USPAT; USOCR	OR	ON	2006/05/17 13:31